37LV36/65/128

36K, 64K, and 128K Serial EPROM Family

FEATURES

- Operationally equivalent to Xilinx[®] XC1700 family
- Wide voltage range 3.0 V to 6.0 V
- Maximum read current 10 mA at 5.0 V
- Standby current 100 μA typical
- Industry standard Synchronous Serial Interface/
 1 bit per rising edge of clock
- · Full Static Operation
- · Sequential Read/Program
- · Cascadable Output Enable
- 10 MHz Maximum Clock Rate @ 5.0 Vdc
- · Programmable Polarity on Hardware Reset
- Programming with industry standard EPROM programmers
- Electrostatic discharge protection > 4,000 volts
- 8-pin PDIP/SOIC and 20-pin PLCC packages
- Data Retention > 200 years
- · Temperature ranges:

Commercial: 0°C to +70°C
 Industrial: -40°C to +85°C

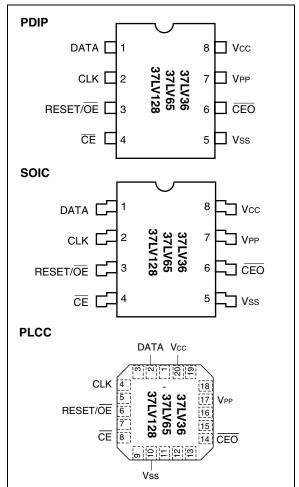
DESCRIPTION

The Microchip Technology Inc. 37LV36/65/128 is a family of Serial OTP EPROM devices organized internally in a x32 configuration. The family also features a cascadable option for increased memory storage where needed. The 37LV36/65/128 is suitable for many applications in which look-up table information storage is desirable and provides full static operation in the 3.0V to 6.0V Vcc range. The devices also support the industry standard serial interface to the popular RAM-based Field Programmable Gate Arrays (FPGA). Advanced CMOS technology makes this an ideal bootstrap solution for today's high speed SRAM-based FPGAs. The 37LV36/65/128 family is available in the standard 8-pin plastic DIP, 8-pin SOIC and 20-pin PLCC packages.

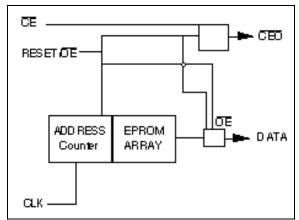
Device	Bits	Programming Word
37LV36	36,288	1134 x 32
37LV65	65,536	2048 x 32
37LV128	131,072	4096 x 32

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PACKAGE TYPES



BLOCK DIAGRAM



1.0 ELECTRICAL CHARACTERISTICS

1.1 <u>Maximum Ratings*</u>

Vcc and input voltages w.r.t. Vss0.6V to +0.6	٥V
VPP voltage w.r.t. VSS during programming0.6V to +14.0	ΟV
Output voltage w.r.t. Vss0.6V to Vcc +0.6	٥V
Storage temperature65°C to +150°	,C
Ambient temp. with power applied65°C to +125°	,C
Soldering temperature of leads (10 sec.)+300	°C
ESD protection on all pins \geq 4 k	٠V

^{*}Notice: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

TABLE 1-1: PIN FUNCTION TABLE

Name	Function	8	20
DATA	Data I/O	1	2
CLK	Clock Input	2	4
RESET/OE	Reset Input and Output Enable	3	6
CE	Chip Enable Input	4	8
Vss	Ground	5	10
CEO	Chip Enable Output	6	14
VPP	Programming Voltage Supply	7	17
Vcc	+3.0V to 6.0V Power Supply	8	20
Not Labeled	Not utilized, not connected		

TABLE 1-2: READ OPERATION DC CHARACTERISTICS

$VCC = +3.0 \text{ to } 6.0V$ $Commercial (C): Tamb = 0^{\circ}C \text{ to } +70^{\circ}C$ $Industrial (I): Tamb = -40^{\circ}C \text{ to } +85^{\circ}C$							
Parameter	Symbol	Min.	Max.	Units	Conditions		
DATA, CE, CEO and Reset pins: High level input voltage Low level input voltage High level output voltage Low level output voltage	VIH VIL VOH1 VOH2 VOL	2.0 -0.3 3.86 2.4 —	Vcc 0.8	V V V	IOH = -4 mA VCC ≥ 4.5V IOH = -4 mA VCC ≥ 3.0V IOL = 4.0 mA		
Input Leakage	ILI	-10	10	μΑ	VIN = .1V to VCC		
Output Leakage	ILO	-10	10	μΑ	Vout = .1V to Vcc		
Input Capacitance (all inputs/outputs)	CINT	_	10	pF	Tamb = 25°C; FCLK = 1 MHz (Note 1)		
Operating Current	Icc Read	_	10 2	mA mA	VCC = 6.0V, CLK = 10 MHz VCC = 3.6V, CLK = 2.5 MHz Outputs open		
Standby Current	Iccs	_	100 50	μ Α μ Α	Vcc = 6.0V, CE = 5.8V Vcc = 3.6V, CE = 3.4V		

Note 1: This parameter is initially characterized and not 100% tested.

2.0 DATA

2.1 Data I/O

Three-state DATA output for reading and input during programming.

3.0 CLK

3.1 Clock Input

Used to increment the internal address and bit counters for reading and programming.

4.0 RESET/OE

4.1 Reset Input and Output Enable

A LOW level on both the $\overline{\text{CE}}$ and RESET/ $\overline{\text{OE}}$ inputs enables the data output driver. A HIGH level on RESET/ $\overline{\text{OE}}$ resets both the address and bit counters. In the 37LVXXX, the logic polarity of this input is programmable as either RESET/ $\overline{\text{OE}}$ or $\overline{\text{OE}/\text{RESET}}$. This document describes the pin as RESET/ $\overline{\text{OE}}$ although the opposite polarity is also possible. This option is defined and set at device program time.

5.0 CE

5.1 Chip Enable Input

CE is used for device selection. A LOW level on both CE and OE enables the data output driver. A HIGH level on CE disables both the address and bit counters and forces the device into a low power mode.

6.0 **CEO**

6.1 Chip Enable Output

This signal is asserted LOW on the clock cycle following the last bit read from the memory. It will stay LOW as long as \overline{CE} and \overline{OE} are both LOW. It will then follow \overline{CE} until \overline{OE} goes HIGH. Thereafter, \overline{CEO} will stay HIGH until the entire EPROM is read again. This pin also used to sense the status of RESET polarity when Programming Mode is entered.

7.0 VPP

7.1 <u>Programming Voltage Supply</u>

Used to enter programming mode (+13 volts) and to program the memory (+13 volts). Must be connected directly to Vcc for normal Read operation. No overshoot above +14 volts is permitted.

8.0 CASCADING SERIAL EPROMS

Cascading Serial EPROMs provide additional memory for multiple FPGAs configured as a daisy-chain, or for future applications requiring larger configuration memories.

When the last bit from the first Serial EPROM is read, the next clock signal to the Serial EPROM asserts its $\overline{\text{CEO}}$ output LOW and disables its DATA line. The second Serial EPROM recognizes the LOW level on its $\overline{\text{CE}}$ input and enables its DATA output.

When configuration is complete, the address counters of all cascaded Serial EPROMs are reset if RESET goes LOW forcing the RESET/OE on each Serial EPROM to go HIGH. If the address counters are not to be reset upon completion, then the RESET/OE inputs can be tied to ground.

Additional logic may be required if cascaded memories are so large that the rippled chip enable is not fast enough to activate successive Serial EPROMs.

9.0 STANDBY MODE

The 37LVXXX enters a low-power Standby Mode whenever \overline{CE} is HIGH. In Standby Mode, the Serial EPROM consumes less than 100 μA of current. The output will remain in a high-impedance state regardless of the state of the \overline{OE} input.

10.0 PROGRAMMING MODE

Programming Mode is entered by holding VPP HIGH (+13 volts) for two clock edges and then holding VPP = VDD for one clock edge. Programming mode is exited by driving a LOW on both \overline{CE} and \overline{OE} and then removing power from the device. Figures 4 through 7 show the programming algorithm.

11.0 37LVXXX RESET POLARITY

The 37LVXXX lets the user choose the reset polarity as either RESET/OE or OE/RESET. Any third-party commercial programmer should prompt the user for the desired reset polarity.

The programming of the overflow word should be handled transparently by the EPROM programmer; it is mentioned here as supplemental information only.

The polarity is programmed into the first overflow word location, maximum address+1. 00000000 in these locations makes the reset active LOW, FFFFFFFF in these locations makes the reset active HIGH. The default condition is RESET active HIGH.

FIGURE 11-1: READ CHARACTERISTICS TIMING

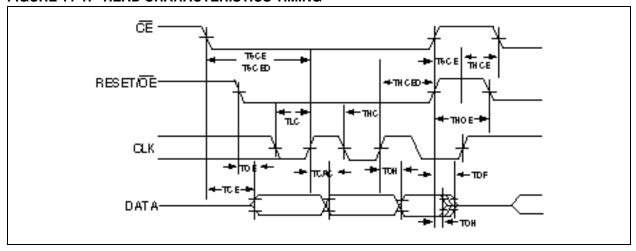


TABLE 11-1: READ CHARACTERISTICS

AC Testing Waveform: VIL = 0.2V; VIH = 3.0V

AC Test Load: 50 pF

Vol = Vol_MAX; Voh = Voh_MIN

	VOL = VOL_IVIIV, VOIT = VOIT_IVIIIV									
Symbol	Parameter	Limits 3.0V ≤ Vcc ≤ 6.0V		Limits 4.5V ≤ Vcc ≤ 6.0V		Units	Conditions			
		Min.	Max.	Min.	Max.					
TOE	OE to Data Delay	_	45	_	45	ns				
TCE	CE to Data Delay	_	60	_	50	ns				
TCAC	CLK to Data Delay	_	200	_	60	ns				
Тон	Data Hold from CE, OE or CLK	0	_	0	_	ns				
TDF	CE or OE to Data Float Delay	_	50	_	50	ns	Notes 1, 2			
TLC	CLK Low Time	100	_	25	_	ns				
Тнс	CLK High Time	100	_	25	_	ns				
TSCE	CE Set up Time to CLK (to guarantee proper counting)	40	_	25	_	ns	Note 1			
TSCED	CE setup time to CLK (to guarantee proper DATA read)	100	_	80	_	ns				
THCE	CE Hold Time to CLK (to guarantee proper counting)	0	_	0	_	ns	Note 1			
THCED	CE hold time to CLK (to guarantee proper DATA read)	50	_	0	_	ns				
Тное	OE High Time (Guarantees counters are Reset)	100		20	_	ns				
CLK max	Clock Frequency	_	2.5	_	10	MHz				

Note 1: This parameter is periodically sampled and not 100% tested.

2: Float delays are measured with output pulled through $1k\Omega$ to VLOAD = VCC/2.

FIGURE 11-2: READ CHARACTERISTICS AT END OF ARRAY TIMING

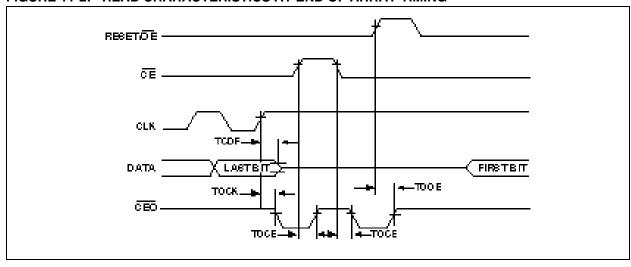


TABLE 11-2: READ CHARACTERISTICS AT END OF ARRAY

AC Testing Waveform: VIL = 0.2V; VIH = 3.0V AC Test Load: 50 pF VOL = VOL_MAX; VOH = VOH_MIN

Symbol	Parameter	Limits 3.0V ≤ Vcc ≤ 6.0V		Limits 4.5V ≤ Vcc ≤ 6.0V		Units	Conditions	
		Min.	Max.	Min.	Max.			
TCDF	CLK to Data Float Delay	_	50	_	50	ns	Notes 1, 2	
Тоск	CLK to CEO Delay	_	65	_	40	ns		
TOCE	CE to CEO Delay	_	45	_	40	ns		
TOOE	RESET/OE to CEO Delay	_	45	_	40	ns		

Note 1: This parameter is periodically sampled and not 100% tested.

^{2:} Float delays are measured with output pulled through $1k\Omega$ to VLOAD = VCC/2.

TABLE 11-3: PIN ASSIGNMENTS IN THE PROGRAMMING MODE

DIP/SOIC Pin	PLCC Pin	Name	I/O	Description
1	2	DATA	I/O	The rising edge of the clock shifts a data word in or out of the EPROM one bit at a time.
2	4	CLK	I	Clock Input. Used to increment the internal address/word counter for reading and programming operation.
3	6	RESET/OE	I	The rising edge of CLK shifts a data word into the EPROM when \overline{CE} and \overline{OE} are HIGH; it shifts a data word out of the EPROM when \overline{CE} is LOW and \overline{OE} is HIGH. The address/word counter is incremented on the rising edge of CLK while \overline{CE} is held HIGH and \overline{OE} is held LOW. Note 1: Any modified polarity of the RESET/ \overline{OE} pin is ignored in the programming mode.
4	8	CE	I	The rising edge of CLK shifts a data word into the EPROM when \overline{CE} and \overline{OE} are HIGH; it shifts a data word out of the EPROM when \overline{CE} is LOW and \overline{OE} is HIGH. The address/word counter is incremented on the rising edge of CLK while \overline{CE} is held HIGH and \overline{OE} is held LOW.
5	10	Vss		Ground pin.
6	14	CEO	0	The polarity of the RESET/OE pin can be read by sensing the CEO pin. Note 1: The polarity of the RESET/OE pin is ignored while in the Programming Mode. In final verification, this pin must be monitored to go LOW one clock cycle after the last data bit has been read.
7	17	VPP		Programming Voltage Supply. Programming Mode is entered by holding \overline{CE} and \overline{OE} HIGH and VPP at VPP1 for two rising clock edges and then lowering VPP to VPP2 for one more rising clock edge. A word is programmed by strobing the device with VPP for the duration TPGM. VPP must be tied to VCC for normal read operation.
8	20	Vcc		+5 V power supply input.

TABLE 11-4: DC PROGRAMMING SPECIFICATIONS

0	A 11 17 1 1 0500 1500	Lin					
Symbol	Parameter Ambient Temperature: Tamb = 25°C ±5°C	Min.	Max.	Units			
VCCP	Supply voltage during programming	5.0	6.0	V			
VIL	Low-level input voltage	0.0	0.5	V			
ViH	High-level input voltage	2.4	Vcc	V			
Vol	Low-level output voltage	_	0.4	V			
Voн	High-level output voltage	3.7	_	V			
VPP1	Programming voltage*	12.5	13.5	V			
VPP2	Programming Mode access voltage	VCCP	VCCP+1	V			
IPPP	Supply current in Programming Mode	_	100	mA			
IL	Input or output leakage current	-10	10	μΑ			
VCCL	First pass Low-level supply voltage for final verification	2.8	3.0	V			
Vcch	Second pass High-level supply voltage for final verification	6.4	6.6	V			
* No overshoot is permitted on this signal. VPP must not be allowed to exceed 14 volts.							

TABLE 11-5: AC PROGRAMMING SPECIFICATIONS (SEE NOTE 2)

Oh al	Davis and a second seco	Lin	nits	11-2-	
Symbol	Parameter	Min.	Max.	Units	Conditions
TRPP	10% to 90% Rise Time of VPP	1		μs	Note 1
TFPP	90% to 10% Fall Time of VPP	1		μѕ	Note 1
ТРСМ	VPP Programming Pulse Width	.50	1.05	ms	
Tsvc	VPP Setup to CLK for Entering Programming Mode	100		ns	Note 1
TSVCE	CE Setup to CLK for Entering Programming Mode	100		ns	Note 1
TSVOE	OE Setup to CLK for Entering Programming Mode	100		ns	Note 1
Тнус	VPP Hold from CLK for Entering Programming Mode	300		ns	Note 1
TSDP	Data Setup to CLK for Programming	50		ns	
THDP	Data Hold from CLK for Programming	0		ns	
TLCE	CE Low time to clear data latches	100		ns	
Tscc	CE Setup to CLK for Programming/Verifying	100		ns	
Tsic	OE Setup to CLK for Incrementing Address Counter	100		ns	
THIC	OE Hold from CLK for Incrementing Address Counter	0		ns	
Thov	OE Hold from VPP	200		ns	Note 1
TPCAC	CLK to Data Valid		400	ns	
Трон	Data Hold from CLK	0		ns	
TPCE	CE Low to Data Valid		250	ns	

Note 1: This parameter is periodically sampled and not 100% tested.

Note 2: While in Programming Mode, $\overline{\text{CE}}$ should only be changed while $\overline{\text{OE}}$ is HIGH and has been HIGH for 200 ns, and $\overline{\text{OE}}$ should only be changed while $\overline{\text{CE}}$ is HIGH and has been HIGH for 200 ns.

FIGURE 11-3: ENTER AND EXIT PROGRAMMING MODES

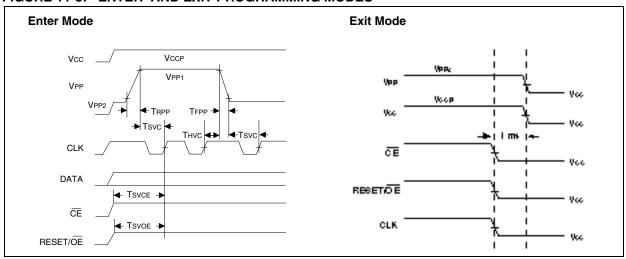


FIGURE 11-4: PROGRAMMING CYCLE OVERVIEW (NO VERIFY UNTIL ENTIRE ARRAY IS PROGRAMMED)

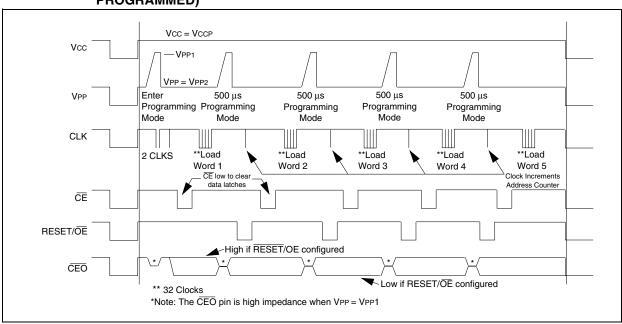


FIGURE 11-5: DETAILS OF PROGRAM CYCLE

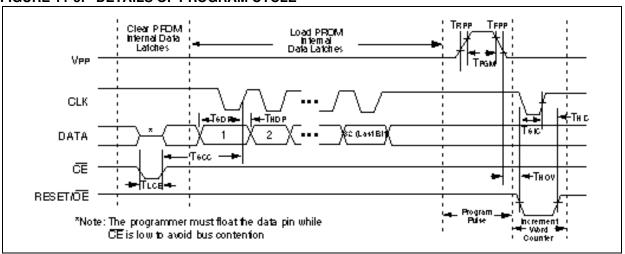


FIGURE 11-6: READ MANUFACTURER AND DEVICE ID OVERVIEW

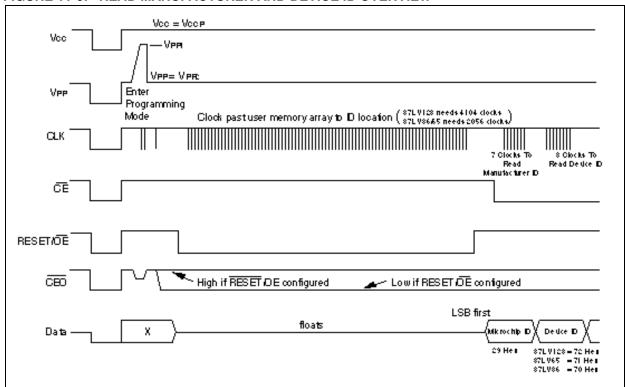


FIGURE 11-7: DETAILS OF READ MANUFACTURER AND DEVICE ID

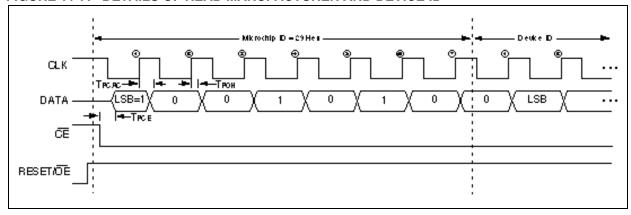
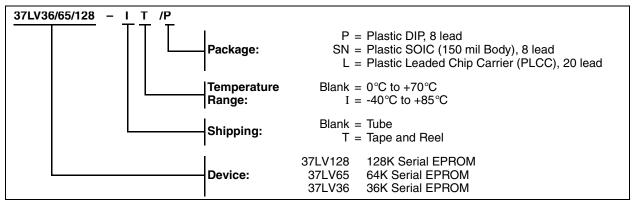


FIGURE 11-8: 37LVXXX PROGRAMMING SPECIFICATIONS Start Check Device ID Device Power Off Device Power On Enter Programming Mode $VCC = VCCP VPP = VPP2 \overline{CE} = \overline{OE} = VIH$ 2. VPP = VPP1 for 2 CLK Rising Edges VPP = VPP2 for 1 CLK Rising Edge 3. Yes 32 bit data word to be programmed = FFFFFFFhex CE low to clear EPROM internal data latches Load 32-bit word to be programmed Pulse VPP to VPP1 (13V) for Tpgm $(500 \, \mu s)$ Increment Address Counter No Last Word? Yes Exit Programming Mode **Device Power Off** Device Power On Verify Yes Fail All Data Bits (Read Mode) 1st Pass? VCC = VPP = VCCL and VCC = VPP = VCCH , No Device Failure Pass Device Passed

37LV36/65/128 Product Identification System

To order or to obtain information, e.g., on pricing or delivery, please use the listed part numbers, and refer to the factory or the listed sales offices.





WORLDWIDE SALES AND SERVICE

AMERICAS

Corporate Office

Microchip Technology Inc. 2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-786-7200 Fax: 480-786-7277 Technical Support: 480-786-7627 Web Address: http://www.microchip.com

Atlanta

Microchip Technology Inc. 500 Sugar Mill Road, Suite 200B Atlanta, GA 30350 Tel: 770-640-0034 Fax: 770-640-0307

Boston

Microchip Technology Inc. 5 Mount Royal Avenue Marlborough, MA 01752 Tel: 508-480-9990 Fax: 508-480-8575

Chicago

Microchip Technology Inc. 333 Pierce Road, Suite 180 Itasca, IL 60143

Tel: 630-285-0071 Fax: 630-285-0075

Dallas

Microchip Technology Inc. 4570 Westgrove Drive, Suite 160 Addison, TX 75248 Tel: 972-818-7423 Fax: 972-818-2924

Dayton

Microchip Technology Inc. Two Prestige Place, Suite 150 Miamisburg, OH 45342

Tel: 937-291-1654 Fax: 937-291-9175

Detroit

Microchip Technology Inc. Tri-Atria Office Building 32255 Northwestern Highway, Suite 190 Farmington Hills, MI 48334 Tel: 248-538-2250 Fax: 248-538-2260

Los Angeles

Microchip Technology Inc. 18201 Von Karman, Suite 1090 Irvine, CA 92612 Tel: 949-263-1888 Fax: 949-263-1338

New York

Microchip Technology Inc. 150 Motor Parkway, Suite 202 Hauppauge, NY 11788 Tel: 631-273-5305 Fax: 631-273-5335

San Jose

Microchip Technology Inc. 2107 North First Street, Suite 590 San Jose, CA 95131 Tel: 408-436-7950 Fax: 408-436-7955

AMERICAS (continued)

Toronto

Microchip Technology Inc. 5925 Airport Road, Suite 200 Mississauga, Ontario L4V 1W1, Canada Tel: 905-405-6279 Fax: 905-405-6253

ASIA/PACIFIC

Hong Kong

Microchip Asia Pacific Unit 2101, Tower 2 Metroplaza 223 Hing Fong Road Kwai Fong, N.T., Hong Kong Tel: 852-2-401-1200 Fax: 852-2-401-3431

Beijing

Microchip Technology, Beijing Unit 915, 6 Chaoyangmen Bei Dajie Dong Erhuan Road, Dongcheng District New China Hong Kong Manhattan Building Beijing 100027 PRC Tel: 86-10-85282100 Fax: 86-10-85282104

India

Microchip Technology Inc. India Liaison Office No. 6, Legacy, Convent Road Bangalore 560 025, India Tel: 91-80-229-0061 Fax: 91-80-229-0062

Japan

Microchip Technology Intl. Inc. Benex S-1 6F 3-18-20, Shinyokohama Kohoku-Ku, Yokohama-shi Kanagawa 222-0033 Japan Tel: 81-45-471- 6166 Fax: 81-45-471-6122

Korea

Microchip Technology Korea 168-1, Youngbo Bldg. 3 Floor Samsung-Dong, Kangnam-Ku Seoul, Korea Tel: 82-2-554-7200 Fax: 82-2-558-5934

Shanghai

Microchip Technology RM 406 Shanghai Golden Bridge Bldg. 2077 Yan'an Road West, Hong Qiao District Shanghai, PRC 200335 Tel: 86-21-6275-5700 Fax: 86 21-6275-5060

ASIA/PACIFIC (continued)

Singapore

Microchip Technology Singapore Pte Ltd. 200 Middle Road #07-02 Prime Centre Singapore 188980

Tel: 65-334-8870 Fax: 65-334-8850

Taiwan, R.O.C

Microchip Technology Taiwan 10F-1C 207 Tung Hua North Road Taipei, Taiwan, ROC Tel: 886-2-2717-7175 Fax: 886-2-2545-0139

EUROPE

United Kingdom

505 Eskdale Road Winnersh Triangle Wokingham Berkshire, England RG41 5TU Tel: 44 118 921 5858 Fax: 44-118 921-5835

Arizona Microchip Technology Ltd.

Denmark

Microchip Technology Denmark ApS Regus Business Centre Lautrup hoj 1-3 Ballerup DK-2750 Denmark Tel: 45 4420 9895 Fax: 45 4420 9910

France

Arizona Microchip Technology SARL Parc d'Activite du Moulin de Massy 43 Rue du Saule Trapu Batiment A - Ier Etage 91300 Massy, France Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany

Arizona Microchip Technology GmbH Gustav-Heinemann-Ring 125 D-81739 München, Germany Tel: 49-89-627-144 0 Fax: 49-89-627-144-44

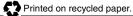
Italy

Arizona Microchip Technology SRL Centro Direzionale Colleoni Palazzo Taurus 1 V. Le Colleoni 1 20041 Agrate Brianza Milan, Italy Tel: 39-039-65791-1 Fax: 39-039-6899883



Microchip received QS-9000 quality system certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona in July 1999. The Company's quality system processes and procedures are QS-9000 compliant for its PICmicro® 8-bit MCUs, KEELOQ® code hopping devices, Serial EEPROMs and microperipheral products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001 certified.

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